

IN THE CLAIMS:

Please cancel claims 5 and 15, without prejudice, and substitute for corresponding pending claims the claims as shown rewritten below with amendments effected therein. Appendix I is attached hereto having marked versions of said claims with amendments indicated by brackets and underlining.

A' 1. (Amended) A dry etching process including:

providing a substrate having a plurality of stacked layers including metal layers and a base of glass;

introducing a processing gas into a vacuum chamber to achieve a predetermined controlled pressure level therein;

applying radio frequency power to a substrate placed within the vacuum chamber for generating plasma in the vacuum chamber, whereby the substrate is processed;

etching the layers on the substrate with the processing gas until a time point when the surface of a lowermost layer on the substrate is etched; and

adding CHF₃ gas to the processing gas for etching the lowermost layer on the substrate, wherein the processing gas is one of Cl₂ and a gaseous mixture containing Cl₂.